

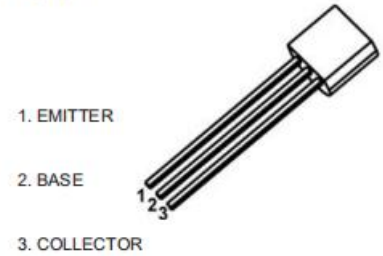
TO-92 Bipolar Transistor 双极型三极管

■ **Features 特点**

PNP High Voltage 高压

■ **Absolute Maximum Ratings 最大额定值**

TO-92



Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Collector-Base Voltage 集电极基极电压	V_{CBO}	-160	V
Collector-Emitter Voltage 集电极发射极电压	V_{CEO}	-150	V
Emitter-Base Voltage 发射极基极电压	V_{EBO}	-5	V
Collector Current 集电极电流	I_C	-600	mA
Power dissipation 耗散功率	$P_C(T_a=25^\circ\text{C})$	625	mW
Thermal Resistance Junction-Ambient 热阻	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+150 $^\circ\text{C}$	

■ **Device Rank 产品分档**

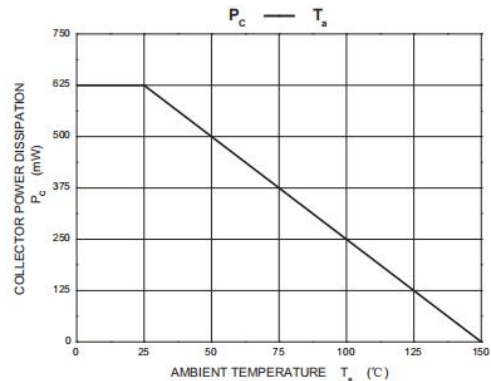
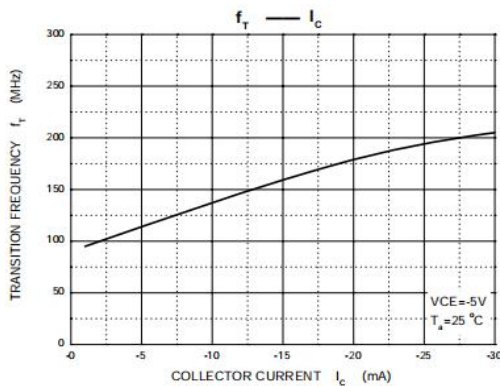
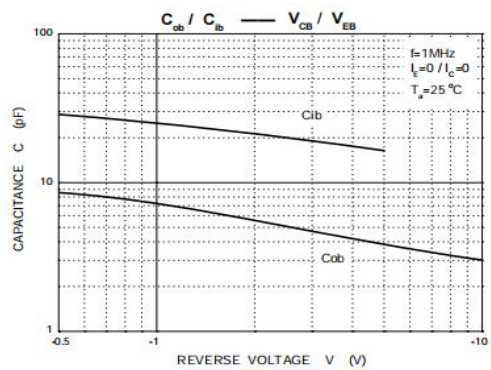
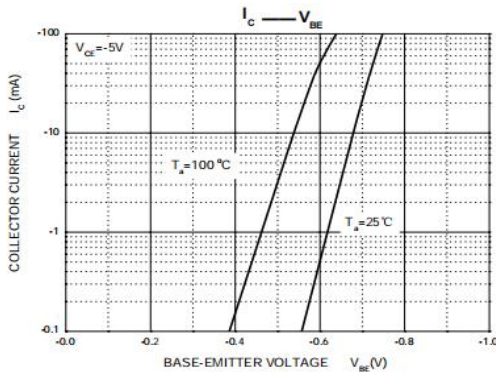
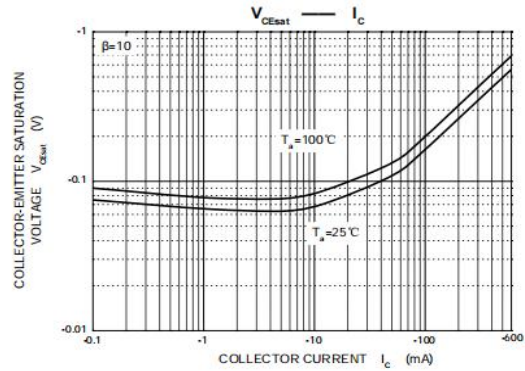
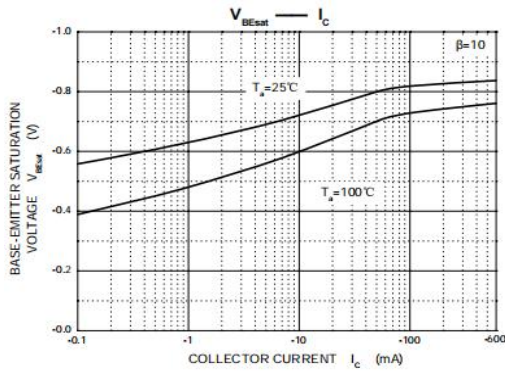
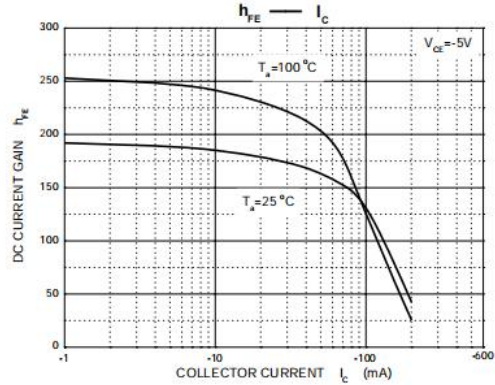
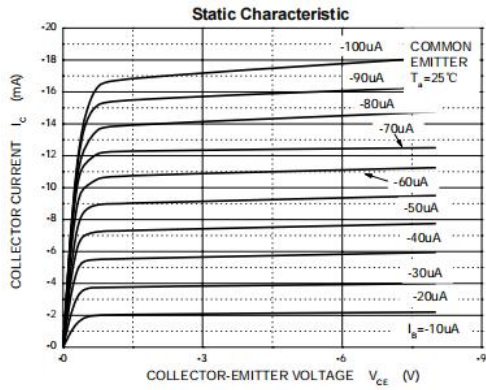
Rank 档位	A	B
$H_{FE} (2)$ Range	100-200	200-300

■ Electrical Characteristics 电特性

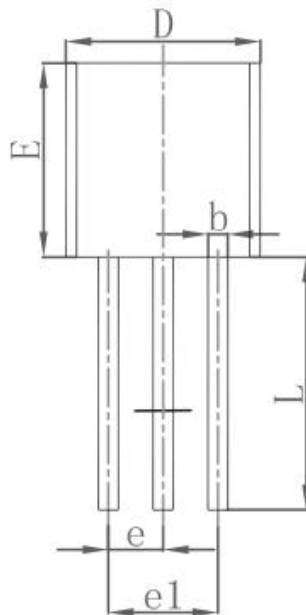
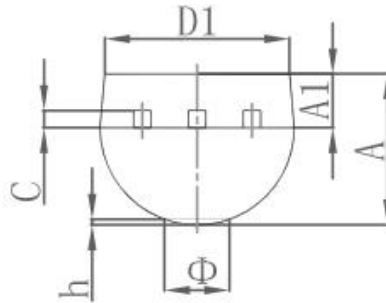
($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	Min 最小值	Type 典型值	Max 最大值	Unit 单位
Collector-Base Breakdown Voltage 集电极基极击穿电压($I_C = -100\mu\text{A}$, $I_E = 0$)	BV_{CBO}	-160	—	—	V
Collector-Emitter Breakdown Voltage 集电极发射极击穿电压($I_C = -1\text{mA}$, $I_B = 0$)	BV_{CEO}	-150	—	—	V
Emitter-Base Breakdown Voltage 发射极基极击穿电压($I_E = -10\mu\text{A}$, $I_C = 0$)	BV_{EBO}	-5	—	—	V
Collector-Base Leakage Current 集电极基极漏电流($V_{CB} = -160\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-100	nA
Collector-Emitter Leakage Current 集电极发射极漏电流($V_{CE} = -120\text{V}$, $I_B = 0$)	I_{CEO}	—	—	-100	nA
Emitter-Base Leakage Current 发射极基极漏电流($V_{EB} = -5\text{V}$, $I_C = 0$)	I_{EBO}	—	—	-100	nA
DC Current Gain 直流电流增益($V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$)	$H_{FE(1)}$	80	—	—	
DC Current Gain 直流电流增益($V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$)	$H_{FE(2)}$	100	—	300	
DC Current Gain 直流电流增益($V_{CE} = -5\text{V}$, $I_C = -100\text{mA}$)	$H_{FE(3)}$	50	—	—	
Collector-Emitter Saturation Voltage 集电极发射极饱和压降($I_C = -10\text{mA}$, $I_B = -1\text{mA}$) ($I_C = -50\text{mA}$, $I_B = -5\text{mA}$)	$V_{CE(sat)}$	—	—	-0.2 -0.5	V
Base-Emitter Saturation Voltage 基极发射极饱和压降($I_C = -10\text{mA}$, $I_B = -1\text{mA}$) ($I_C = -50\text{mA}$, $I_B = -5\text{mA}$)	$V_{BE(sat)}$	—	—	-1 -1	V
Transition Frequency 特征频率($V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$)	f_T	100	—	—	MHz
Output Capacitance 输出电容($V_{CB} = -5\text{V}$, $I_E = 0$, $f = 1\text{MHz}$)	C_{ob}	—	6	—	pF

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Φ		1.600		0.063
h	0.000	0.380	0.000	0.015